

Product Overview

FGH40T120SQDNL4: IGBT, Ultra Field Stop

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Ultra Field Stop Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
 - $T_{Jmax} = 175^{\circ}C$
 - Soft Fast Reverse Recovery Diode
 - Optimized for High Speed Switching
 - These are Pb-Free Devices

Applications

- Solar inverter
- UPS
- Welding

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	$V_{CE(s)}$ Typ (V)	I_C Max (A)	$V_{CE(s)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
FGH40T120SQDNL4	3.9466	Pb-free Halide free	Active	1200	40	1.78	3.4	1.1	2.7	166	9	221	0		227	Yes	TO-247-4

For more information please contact your local sales support at www.onsemi.com.

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